TIL197, TIL198, TIL199, TIL197A, TIL198A, TIL199A TIL197B, TIL198B, TIL199B SINGLE/DUAL/QUAD CHANNEL OPTOCOUPLERS/OPTOISOLATORS

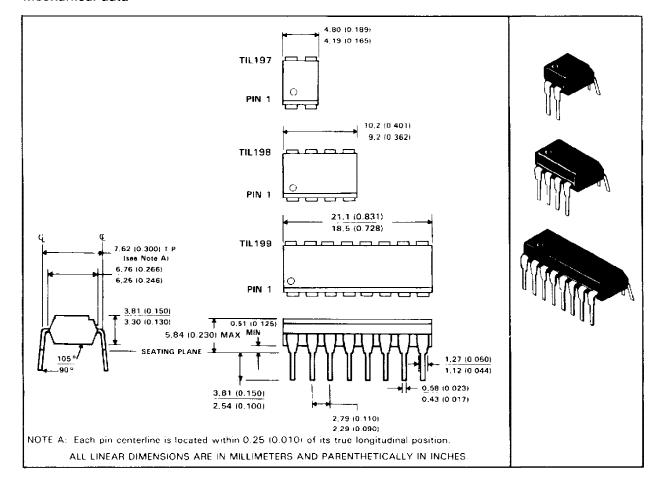
SOOS023 D3437, MAY 1990

- Gallium-Arsenide Diode Infrared Source
- Source Is Optically Coupled to Silicon N-P-N Darlington Phototransistor
- . Choice of One, Two or Four Channels
- Choice of Three Current-Transfer Ratios
- High-Voltage Electrical Isolation 3.535 kV Peak (2.5 kV rms)
- Plastic Dual-In-Line Packages
- UL Listed File #E65085

description

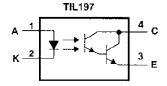
These optocouplers consist of a gallium-arsenide light-emitting diode and a silicon n-p-n Darlington phototransistor per channel. The TIL197 has one channel in a 4-pin package, the TIL198 has two channels in a 8-pin package, and the TIL199 has four channels in a 16-pin package. The standard devices, TIL197, TIL198, and TIL199, are tested for a current-transfer ratio of 500% minimum. Devices selected for a current-transfer ratio of 1000% and 1500% minimum are designated with the suffixes A and B, respectively.

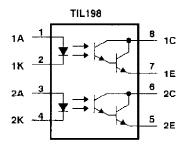
mechanical data

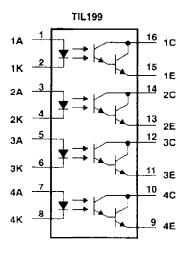


TIL197, TIL198, TIL199, TIL197A, TIL198A, TIL199A TIL197B, TIL198B, TIL199B SINGLE/DUAL/QUAD CHANNEL OPTOCOUPLERS/OPTOISOLATORS

schematic diagrams







absolute maximum ratings at 25°C free-air temperature (unless otherwise noted)

Input-to-output voltage (see Note 1)	±3.535 kV peak or dc (+2.5 kV rms)
Collector-emitter voltage (see Note 2)	
Emitter-collector voltage	
Input diode reverse voltage	
Input diode continuous forward current at (or below) 25°C free-air temper	
Continuous power dissipation at (or below) 25°C free-air temperature:	
Phototransistor (see Note 4)	150 mW
Input diode plus phototransistor per channel (see Note 5)	200 mW
Storage temperature range	– 55°C to 125°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

NOTE 1: This rating applies for sine-wave operation at 50 or 60 Hz. Service capability is verified by testing in accordance with UL requirements.

- 2. This value applies when the base-emitter diode is open circuited.
- 3. Derate linearly to 100°C free air temperature at the rate of 0.67 mA/°C.
- 4. Derate linearly to 100°C free-air temperature at the rate of 2 mW/°C.
- 5. Derate linearly to 100°C free-air temperature at the rate of 2.67 mW/°C.

electrical characteristics at 25°C free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT	
V(BR)CEO	Collector-emitter breakdown voltage Emitter-collector breakdown voltage Input diode static reverse current		$I_C = 0.5 \text{ mA}, \qquad I_F = 0$ $I_C = 100 \mu\text{A}, \qquad I_F = 0$ $V_R = 5 \text{ V}$		35			V
V _(BR) EÇO					7			V
¹ R							10	μΑ
^I C(off)	Off-state co	ollector current	V _{CE} = 10 V,	IF = 0			100	nA
•	Current	TIL197, TIL198, TIL199			500%			
CTR	transfer	TIL197A, TIL198A, TIL199A	IF = 2 mA,	V _{CE} = 1 V	1000%			
	ratio	TIL197B, TIL198B, TIL199B	1		1500%			
٧ _F	Input diodo static forward voltage		lp = 20 mA				1.4	٧
VCE(sat)	Collector-emitter saturation voltage		l _F = 10 mA,	IC = 50 mA			1	٧
Cio	Input-to-output capacitance		V _{in-out} = 0,	f = 1 MHz, See Note 6		1		ρF
rio	Input-to-output internal resistance		V _{in-out} = ±1 kV.	See Note 6		1011		Ω

NOTE 6. These parameters are measured between all input-diode leads shorted together and all phototransistor leads shorted together.

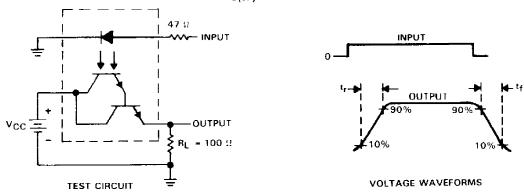


switching characteristics at 25°C free-air temperature

PARAMETER	TEST CONDITIONS		TYP	UNIT
t _r Rise time	V _{CC} = 10 V,	I _{C(on)} = 10 mA,	100	
t _f Fall time	$R_L = 100 \Omega$,	See Figure 1	100	us

PARAMETER MEASUREMENT INFORMATION

Adjust amplitude of input pulse for |C(on) = 10 mA

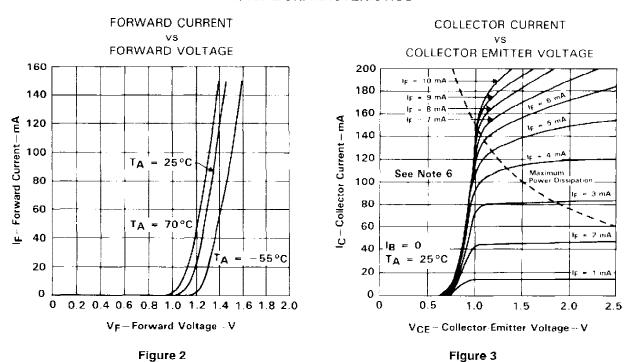


NOTES: A. The input waveform is supplied by a generator with the following characteristics: $Z_0 = 50 \, \Omega_{\rm t} \, t_{\rm f} \le 15 \, \rm ns$, duty cycle = 1%, $t_{\rm W} = 500 \, \mu \rm s$.

B. The output waveform is monitored on an oscilloscope with the following characteristics: $t_T = 12$ ns, $R_{\rm in} > 1$ M Ω , $C_{\rm in} < 20$ pF.

Figure 1. Switching Times

TYPICAL CHARACTERISTICS



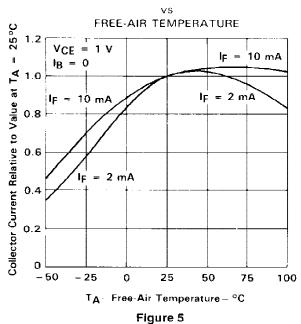
NOTE 6: Pulse operation is required for operation beyond limits shown by the dashed line.

COLLECTOR CURRENT INPUT DIODE FORWARD CURRENT 1000 g 400 $l_B = 0$ - 25°C IC-Collector Current-mA See Note 7 100 40 10 4 0.4 0.1 0.1 40 100 0.4 F Forward Current mA Figure 4

NOTE 7: These parameters were measured using pulse techniques $t_{W} = 1$ ms, duty cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS

RELATIVE ON-STATE COLLECTOR CURRENT



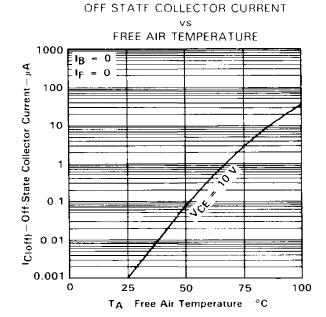


Figure 6

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